

Supplementary Information

Ultrahigh Responsivity Self-powered Solar-blind Photodetector Based on Centimeter-Sized β -Ga₂O₃/Polyaniline Heterojunction

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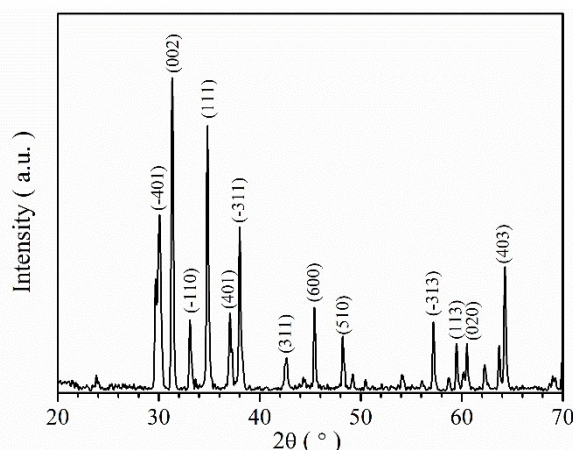


Fig. S1 XRD pattern of Ga₂O₃ microwires. Because it is difficult to measure a single Ga₂O₃ microwire, so we placed multiple samples on the substrate. As shown in the figure, the diffraction peaks agree well with the monoclinic phase of Ga₂O₃.

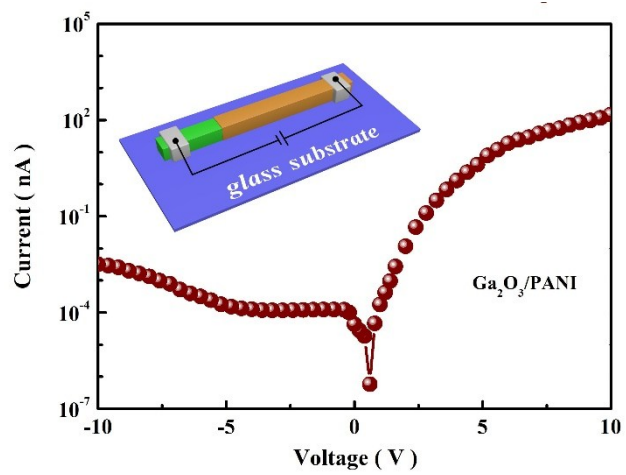


Fig. S2 The I-V curve of $\beta\text{-Ga}_2\text{O}_3/\text{PANI}$ heterojunction in log scale